

18(New). The semiconductor package of claim 17, wherein the solder mask is made from photosensitive and insulative materials selected from the group consisting of polyimide and ultraviolet-curable resins.

19(New). The semiconductor package of claim 18, wherein the lead layer and die pad layer are made of conductive materials selected from the group consisting of nickel and gold.

20(New). The semiconductor package of claim 18, wherein the solder mask is formed by performing photolithography process on a polyimide or ultraviolet-curable resin layer.

21(New). The semiconductor package of claim 17, wherein the lead layer and die pad layer are formed by plating.

22(New). The semiconductor package of claim 17, wherein the conductive elements are made of a material selected from the group consisting of gold, copper and aluminum.

23(New). The semiconductor package of claim 17, wherein the die pad layer is replaced by a solder mask.

24(New). A single semiconductor package consisting essentially of a solder mask layer formed at selected locations and intermediate and contiguous thereto a lead layer and a die pad layer, said die pad layer has a chip adhering to the die pad layer; a plurality of conductive elements are electrically connecting the chip and the lead layer; and a molded resin covering the chip, conductive elements, solder masks, lead layer and die pad layer.

25(New). The semiconductor package of claim 24, wherein the solder mask is made from photosensitive and insulative materials selected from the group consisting of polyimid and ultraviolet-curable resins.

26(New). The semiconductor package of claim 24, wherein the lead layer and die pad layer are made of conductive materials selected from the group consisting of nickel and gold.

27(New). The semiconductor package of claim 24, wherein the solder mask is formed by performing photolithography process on a polyimid or ultraviolet-curable resin layer.

28(New). The semiconductor package of claim 24, wherein the lead layer and die pad layer are formed by plating.

29(New). The semiconductor package of claim 24, wherein the conductive elements are made of a material selected from the group consisting of gold, copper and aluminum.

30(New). The semiconductor package of claim 24, wherein the die pad layer is replaced by a solder mask.

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